



Diode, Wechselrichter / Diode, Inverter

Höchstzulässige Werte / Maximum Rated Values

Periodische Spitzensperrspannung Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1700	V
Dauergleichstrom Continuous DC forward current		I_F	450	A
Periodischer Spitzenstrom Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	900	A
Grenzlastintegral I^2t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	24,0 23,0	kA ² s kA ² s

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Durchlassspannung Forward voltage	$I_F = 450\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$		1,85	2,25	V
	$I_F = 450\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		1,95	2,35	V
	$I_F = 450\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		1,95		V
Rückstromspitze Peak reverse recovery current	$I_F = 450\text{ A}, -di_F/dt = 4200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		490		A
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		540		A
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		565		A
Sperrverzögerungsladung Recovered charge	$I_F = 450\text{ A}, -di_F/dt = 4200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		105		μC
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		180		μC
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		205		μC
Abschaltenergie pro Puls Reverse recovery energy	$I_F = 450\text{ A}, -di_F/dt = 4200\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$	$T_{vj} = 25^{\circ}\text{C}$		56,0		mJ
	$V_R = 900\text{ V}$	$T_{vj} = 125^{\circ}\text{C}$		105		mJ
	$V_{GE} = -15\text{ V}$	$T_{vj} = 150^{\circ}\text{C}$		120		mJ
Wärmewiderstand, Chip bis Gehäuse Thermal resistance, junction to case	pro Diode / per diode	R_{thJC}			100	K/kW
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Diode / per diode $\lambda_{Paste} = 1\text{ W}/(\text{m}\cdot\text{K}) / \lambda_{grease} = 1\text{ W}/(\text{m}\cdot\text{K})$	R_{thCH}		27,0		K/kW
Temperatur im Schaltbetrieb Temperature under switching conditions		$T_{vj\text{ op}}$	-40		150	$^{\circ}\text{C}$

NTC-Widerstand / NTC-Thermistor

Charakteristische Werte / Characteristic Values

			min.	typ.	max.	
Nennwiderstand Rated resistance	$T_C = 25^{\circ}\text{C}$	R_{25}		5,00		k Ω
Abweichung von R100 Deviation of R100	$T_C = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5		5	%
Verlustleistung Power dissipation	$T_C = 25^{\circ}\text{C}$	P_{25}			20,0	mW
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$		3375		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$		3411		K
B-Wert B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$		3433		K

Angaben gemäß gültiger Application Note.
Specification according to the valid application note.

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Modul / Module

Isolations-Prüfspannung Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V _{ISOL}	4,0		kV
Material Modulgrundplatte Material of module baseplate			Cu		
Innere Isolation Internal isolation	Basisisolierung (Schutzklasse 1, EN61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
Kriechstrecke Creepage distance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		33,0 33,0		mm
Luftstrecke Clearance	Kontakt - Kühlkörper / terminal to heatsink Kontakt - Kontakt / terminal to terminal		19,0 19,0		mm
Vergleichszahl der Kriechwegbildung Comperative tracking index		CTI	> 400		
			min. typ. max.		
Wärmewiderstand, Gehäuse bis Kühlkörper Thermal resistance, case to heatsink	pro Modul / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R _{thCH}	4,50		K/kW
Modulstreuinduktivität Stray inductance module		L _{sCE}	18		nH
Modulleitungswiderstand, Anschlüsse - Chip Module lead resistance, terminals - chip	T _c = 25°C, pro Schalter / per switch	R _{CC+EE'}	0,30		mΩ
Lagertemperatur Storage temperature		T _{stg}	-40	150	°C
Anzugsdrehmoment f. Modulmontage Mounting torque for modul mounting	Schraube M5 - Montage gem. gültiger Applikationsschrift Screw M5 - Mounting according to valid application note	M	3,00	-	6,00 Nm
Anzugsdrehmoment f. elektr. Anschlüsse Terminal connection torque	Schraube M4 - Montage gem. gültiger Applikationsschrift Screw M4 - Mounting according to valid application note Schraube M8 - Montage gem. gültiger Applikationsschrift Screw M8 - Mounting according to valid application note	M	1,8	-	2,1 Nm
			8,0	-	10 Nm
Gewicht Weight		G	825		g

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